New Jersey Semi-Conductor Products, Inc.

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Thyristors

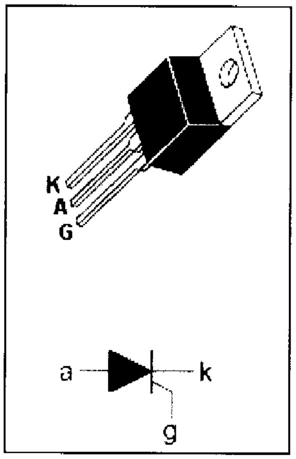
TIC126N

APPLICATIONS

- 12A continmunous on-state current
- 100A surge-current
- Glass passivated
- Max I_{GT} of 20mA

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage	800	V
V_{RRM}	Repetitive peak reverse voltage	800	V
$I_{T(AV)}$	On-state current Tc=80℃	7.5	A
$I_{T(RMS)}$	RMS on-state current Tc=80℃	12	A
I_{TM}	Surge peak on-state current	100	A
P_{GM}	Peak gate power $P_W \leqslant 300\mu s$	5	W
$P_{G(AV)}$	Average gate power	1	W
T_j	Operating Junction temperature	110	℃
T_{stg}	Storage temperature	-40 ~+125	℃
$R_{th(j\text{-}c)}$	Thermal resistance, junction to case	2.4	℃/W
$R_{th(j\text{-}a)}$	Thermal resistance, junction to ambient	62.5	℃/W



ELECTRICAL CHARACTERISTICS (T_C=25℃ unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
I_{RRM}	Repetitive peak reverse current	$V_{RM}=V_{RRM}$, Tj=110℃			2.0	mA
I_{DRM}	Repetitive peak off-state current	$V_{RM}=V_{RRM}$, Tj=110℃			2.0	mA
V_{TM}	On-state voltage	I_{TM}= 12A			1.4	V
I_{GT}	Gate-trigger current	V_{AA}=6V; R_L=100Ω			20	mA
V_{GT}	Gate-trigger voltage	V_{AA}=6V; R_L=100Ω			1.5	V
I_H	Holding current	V_{AA}=6V; R_{GK}=1kΩ ,I_T=100mA			40	mA

Quality Semi-Conductors